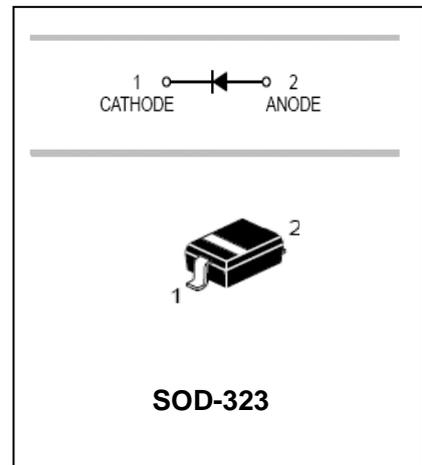


Low-leakage Diode

BAS416

FEATURES

- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μ s
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.



APPLICATIONS

- Low-leakage current applications in surface mounted circuits

ORDERING INFORMATION

Type No.	Marking	Package Code
BAS416	D4	SOD-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RRM}	85	V
DC Reverse Voltage	V_R	75	V
continuous forward current	I_F	200	mA
repetitive peak forward current	I_{FRM}	500	
non-repetitive peak forward current	I_{FSM}	$t = 1 \mu s$	4
		$t = 1 ms$	1
		$t = 1 s$	0.5
Power Dissipation	P_D	250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{STG}	-65 to +125	°C

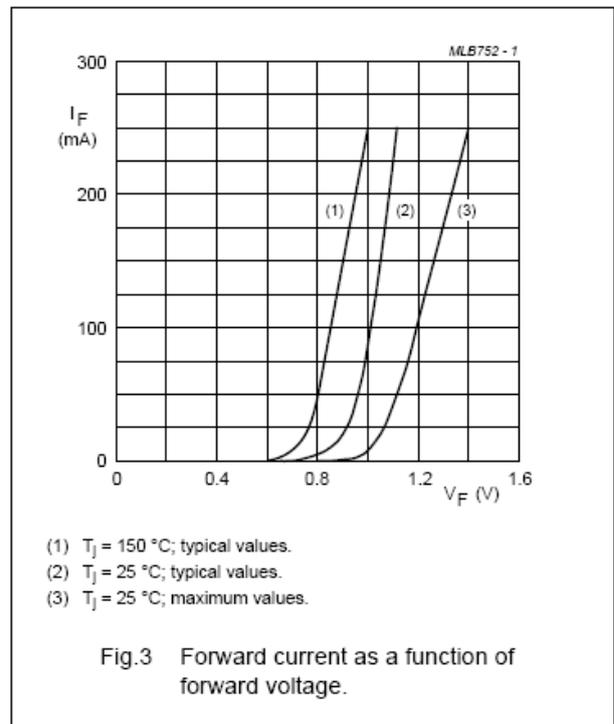
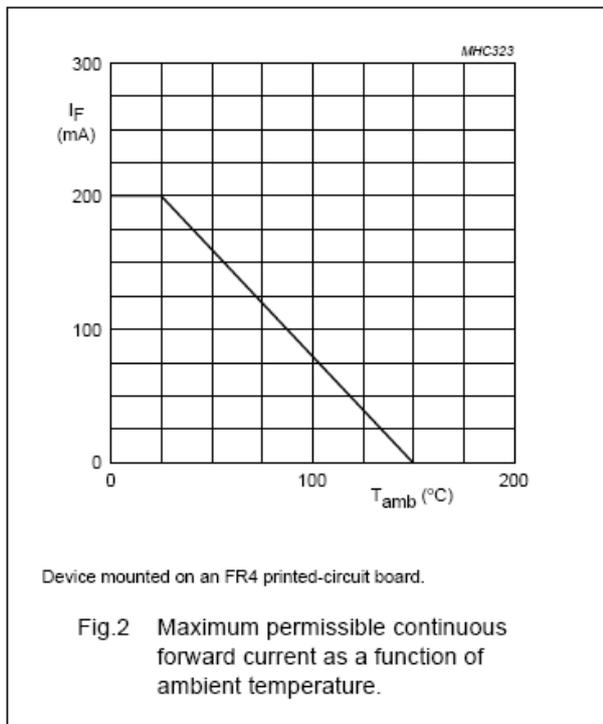
Low-leakage Diode

BAS416

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

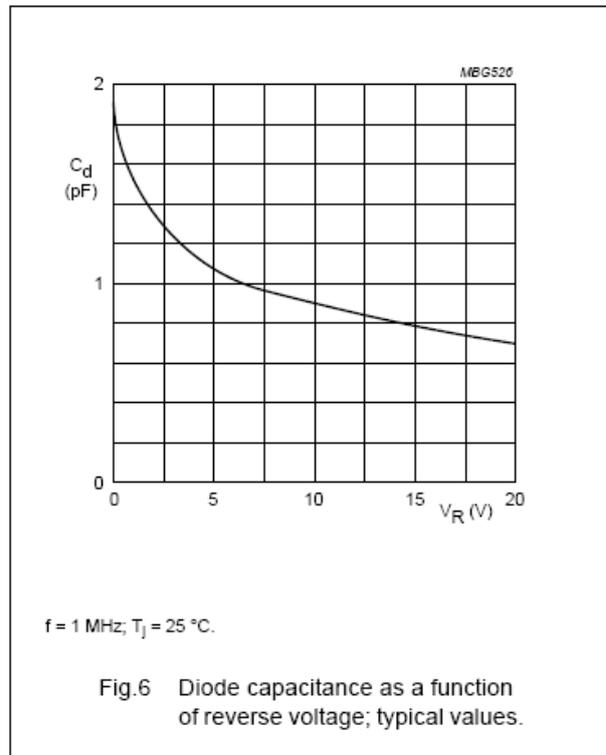
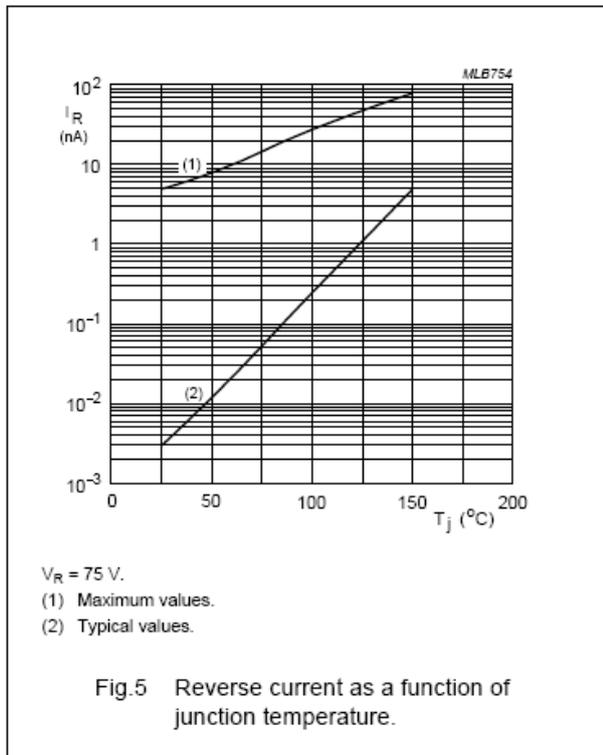
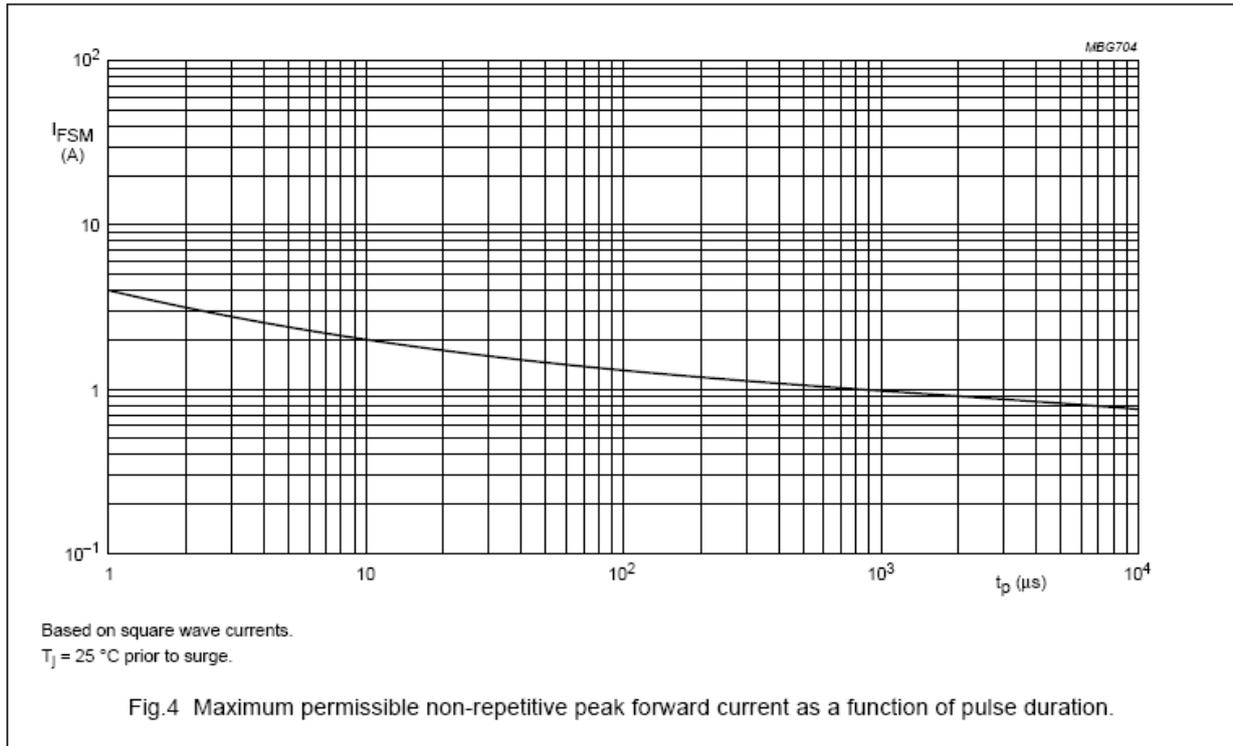
Parameter	Symbol	Min.	TYP.	Max.	Unit	Conditions
Forward voltage	V_F			0.9 1 1.1 1.25	V	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$
Reverse current	I_R			50	μA	$V_R=75\text{V}$
Capacitance between terminals	C_d		2		pF	$V_R=0\text{V}, f=1\text{MHz}$
reverse recovery time	t_{rr}		0.8	3	us	when switched from $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$; $R_L = 100\Omega$ measured at $I_R = 1 \text{ mA}$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Low-leakage Diode

BAS416



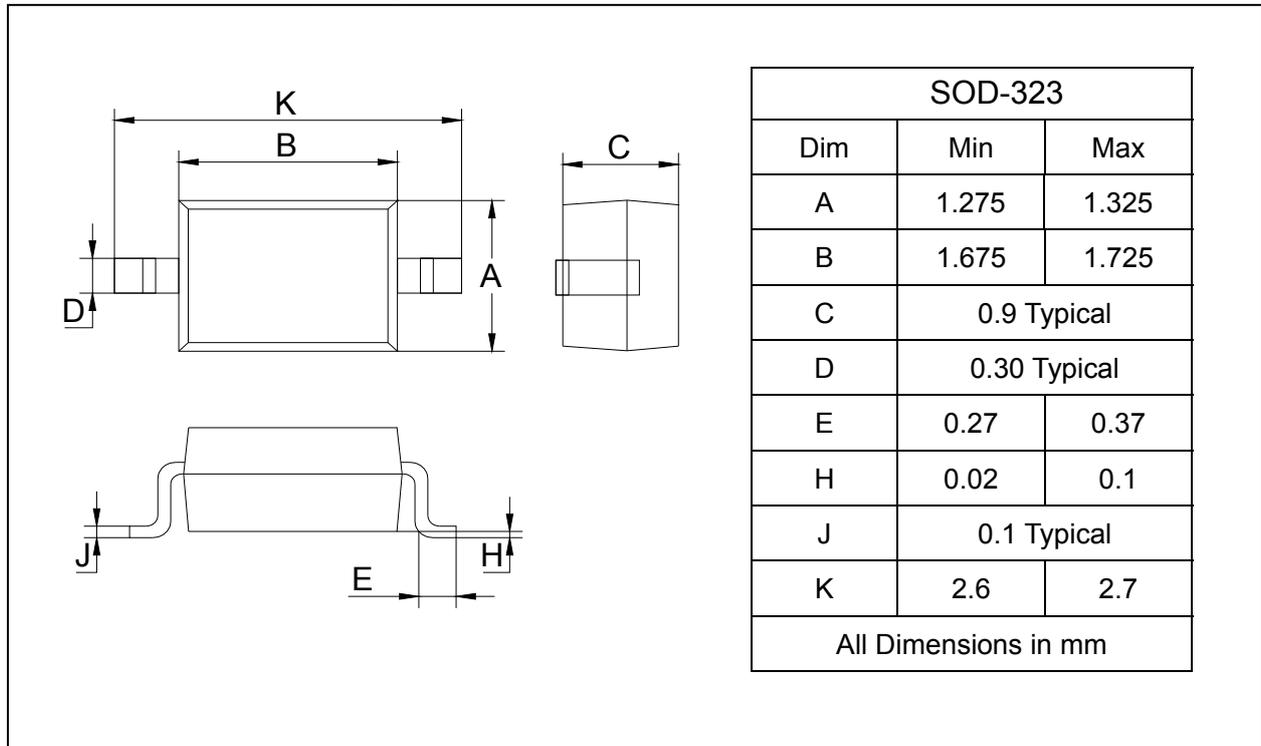
Low-leakage Diode

BAS416

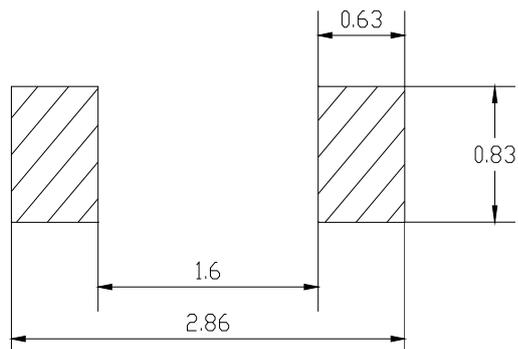
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
BAS416	SOD-323	3000/Tape&Reel